# 2SB727(K)

## Silicon PNP Epitaxial

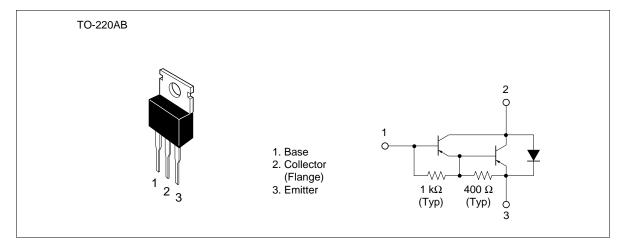
# **HITACHI**

ADE-208-857 (Z) 1st. Edition Sep. 2000

#### **Application**

Medium speed and power switching complementary pair with 2SD768(K)

#### **Outline**



### **Absolute Maximum Ratings** (Ta = 25°C)

Item	Symbol	Rating	Unit
Collector to base voltage	$V_{\scriptscriptstyle \sf CBO}$	-120	V
Collector to emitter voltage	V <sub>CEO</sub>	-120	V
Emitter to base voltage	$V_{EBO}$	<b>-</b> 7	V
Collector current	I <sub>c</sub>	-6	А
Collector peak current	I <sub>C(peak)</sub>	-10	А
Collector power dissipation	P <sub>c</sub> *¹	40	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Note: 1. Value at  $T_c = 25^{\circ}C$ 

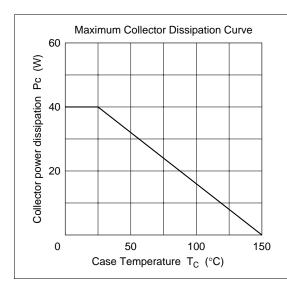


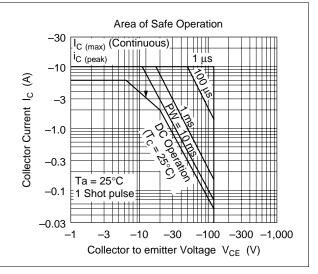
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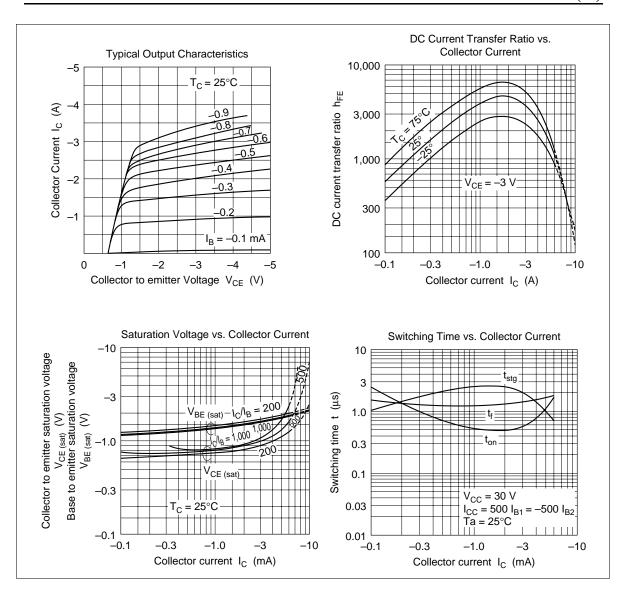
#### **Electrical Characteristics** ( $Ta = 25^{\circ}C$ )

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-120	_	_	V	$I_{\rm C}$ = -25 mA, $R_{\rm BE}$ = $\infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	<b>-7</b>	_	_	V	$I_{\rm E} = -50 \text{ mA}, I_{\rm C} = 0$
Collector cutoff current	I <sub>CBO</sub>	_	_	-100	μΑ	$V_{CB} = -120 \text{ V}, I_{E} = 0$
	I <sub>CEO</sub>	_	_	-10	μΑ	$V_{CE} = -100 \text{ V}, R_{BE} = \infty$
DC current transfer ratio	$h_{\text{FE}}$	1000	_	20000		$V_{CE} = -3 \text{ V}, I_{C} = -3 \text{ A}^{*1}$
Collector to emitter saturation	$V_{\text{CE(sat)1}}$	_	_	-1.5	V	$I_{\rm C} = -3 \text{ A}, I_{\rm B} = -6 \text{ mA}^{*1}$
voltage	$V_{\text{CE}(\text{sat})2}$	_	_	-3.0	V	$I_{\rm C} = -6 \text{ A}, I_{\rm B} = -60 \text{ mA}^{*1}$
Base to emitter saturation	$V_{\text{BE}(\text{sat})1}$	_	_	-2.0	V	$I_{\rm C} = -3 \text{ A}, I_{\rm B} = -6 \text{ mA}^{*1}$
voltage	$V_{\text{BE}(\text{sat})2}$	_	_	-3.5	V	$I_{\rm C} = -6 \text{ A}, I_{\rm B} = -60 \text{ mA}^{*1}$
Turn on time	$\mathbf{t}_{on}$	_	1.0	_	μs	$I_{\rm C} = -3 \text{ A}, I_{\rm B1} = -I_{\rm B2} = -6 \text{ mA}$
Turn off time	t <sub>off</sub>	_	3.0	_	μs	

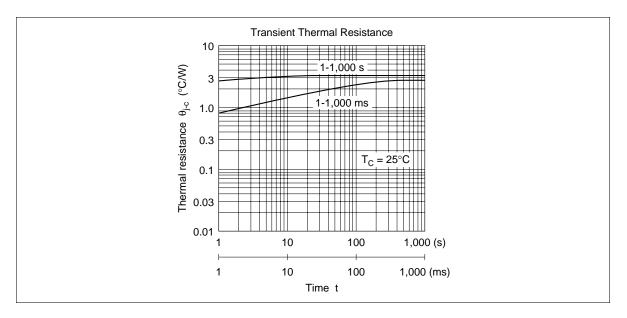
Note: 1. Pulse test



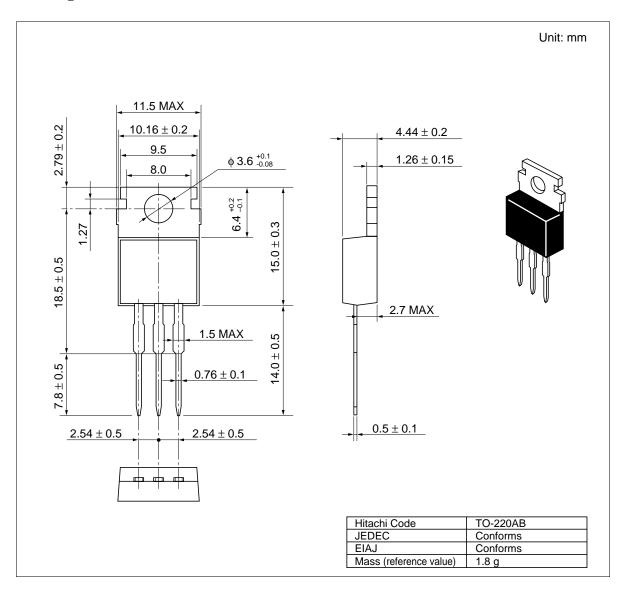




## 2SB727(K)



### **Package Dimensions**



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